

Dual N-Channel 60-V (D-S), 175 °C MOSFET

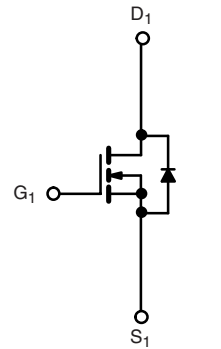
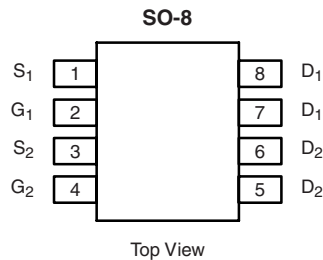
PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
60	0.080 at V _{GS} = 10 V	± 3.7
	0.100 at V _{GS} = 4.5 V	± 3.4

FEATURES

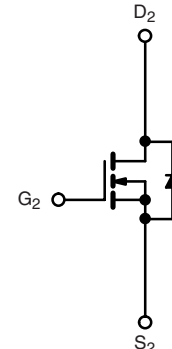
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFETs
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available



N-Channel MOSFET



N-Channel MOSFET

Ordering Information: Si9945AEY-T1-E3 (Lead (Pb)-free)
Si9945AEY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	60	V	
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current (T _J = 175 °C) ^a	I _D	T _A = 25 °C	A	
		T _A = 70 °C		
Pulsed Drain Current	I _{DM}	25		
Continuous Source Current (Diode Conduction) ^a	I _S	2		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	W	
		T _A = 70 °C		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Junction-to-Ambient ^a	R _{thJA}	t ≤ 10 s	62.5	°C/W	
		Steady State	93		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.